

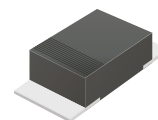
CSFMT101-HF Thru. CSFMT108-HF

Reverse Voltage: 50 to 600 Volts

Forward Current: 1.0 Amp

RoHS Device

Halogen Free

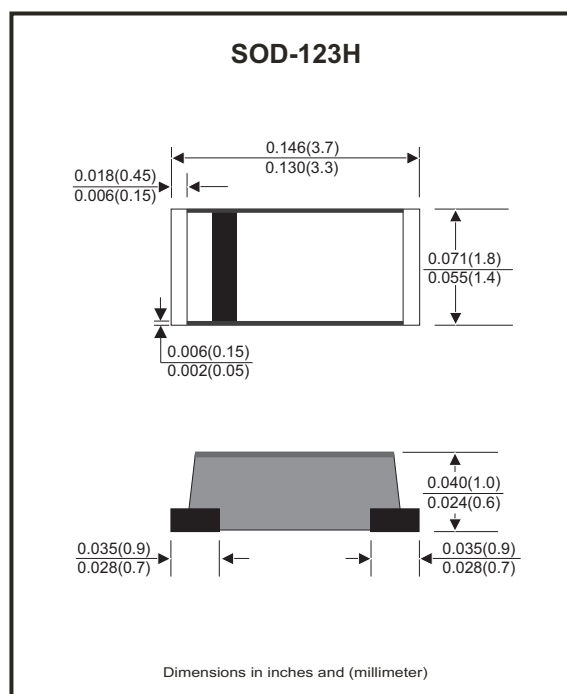


Features

- Excellent power dissipation offers better reverse leakage current and thermal resistance.
- Low profile surface mounted application in order to optimize board space.
- Tiny plastic SMD package.
- High current capability.
- Super fast recovery time for switching mode application.
- High surge current capability.
- Glass passivated chip junction.

Mechanical data

- Epoxy: UL94V-0 rated flame retardant.
- Case: Molded plastic, SOD-123H/MINI SMA
- Terminals: Solderable per MIL-STD-750, Method 2026.
- Polarity: Indicated by cathode band.
- Mounting Position: any
- Weight: 0.011 grams approx.



Maximum Ratings and Electrical Characteristics (at T_A=25°C unless otherwise noted)

Parameter	Symbol	CSFMT 101-HF	CSFMT 102-HF	CSFMT 103-HF	CSFMT 104-HF	CSFMT 105-HF	CSFMT 106-HF	CSFMT 107-HF	CSFMT 108-HF	Unit
Max. repetitive peak reverse voltage	V _{RRM}	50	100	150	200	300	400	500	600	V
Max. Continuous rever voltage	V _R	50	100	150	200	300	400	500	600	V
Max. RMS voltage	V _{RMS}	35	70	105	140	210	280	350	420	V
Max. Forward rectified current	I _O	1.0								A
Max. Forward voltage @ I _F =1.0A	V _F	0.95				1.25		1.70		V
Reverse recovery time (Note 1)	T _{RR}	35								ns
Max. Forward surge current 8.3ms singe half sine-wave superimposed on rated load (JEDEC method)	I _{FSM}	25								A
Max. Reverse current	V _R =V _{RRM} T _J =25°C	I _R	5.0							μA
	V _R =V _{RRM} T _J =125°C		100							
Typ. Thermal resistance Junction to ambient air	R _{θJA}	42								°C/W
Typ. Junction capacitance f=1MHz and applied 4V DC reverse voltage	C _J	10								pF
Operating junction temperature	T _J	-55 to +150								°C
Storage temperature	T _{STG}	-65 to +175								°C

Note 1. Reverse recovery time test condition, I_F=0.5A, I_R=1.0A, I_{RR}=0.25A

2. Company reserves the right to improve product design , functions and reliability without notice.

REV: B

Rating and Characteristic Curves (CSFMT101-HF Thru. CSFMT108-HF)

Fig.1 - Typical Forward Current Derating Curve

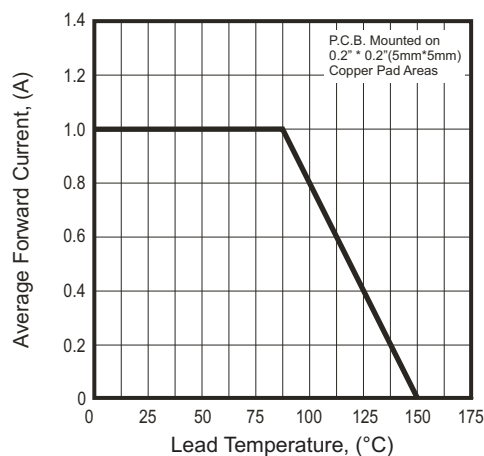


Fig.2 - Typical Forward Characteristics

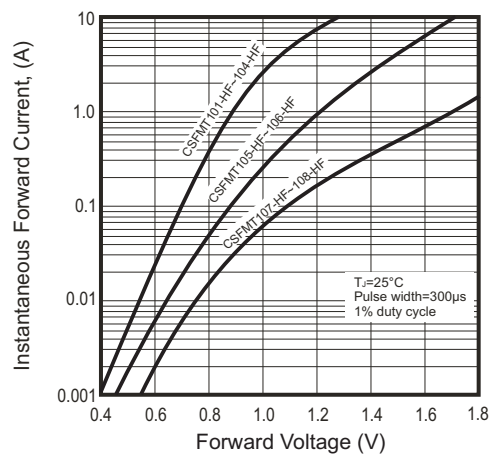
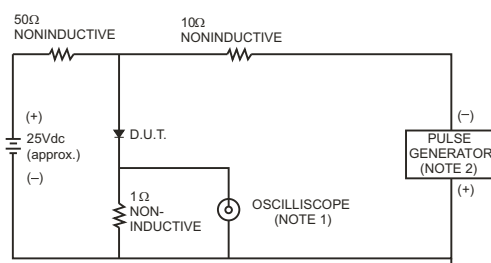


Fig.3- Test Circuit Diagram and Reverse Recovery Time Characteristics



NOTES: 1. Rise Time= 7ns max., Input Impedance= 1 megohm.22pF.
2. Rise Time= 10ns max., Source Impedance= 50 ohms.

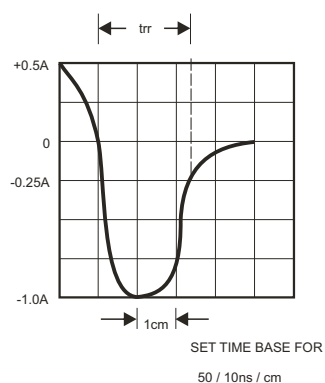


Fig.4 - Maximum Non-repetitive Forward Surge Current

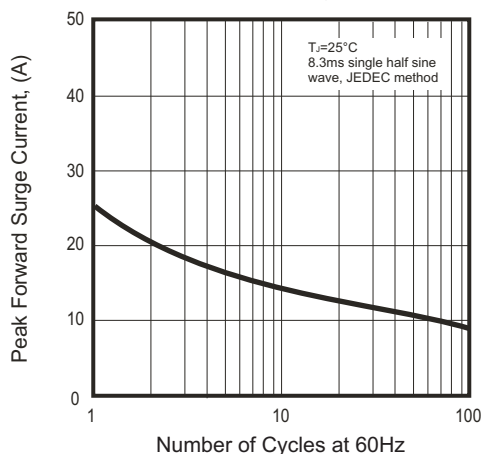
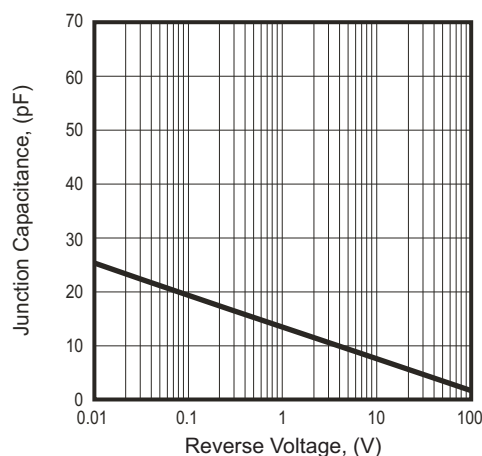
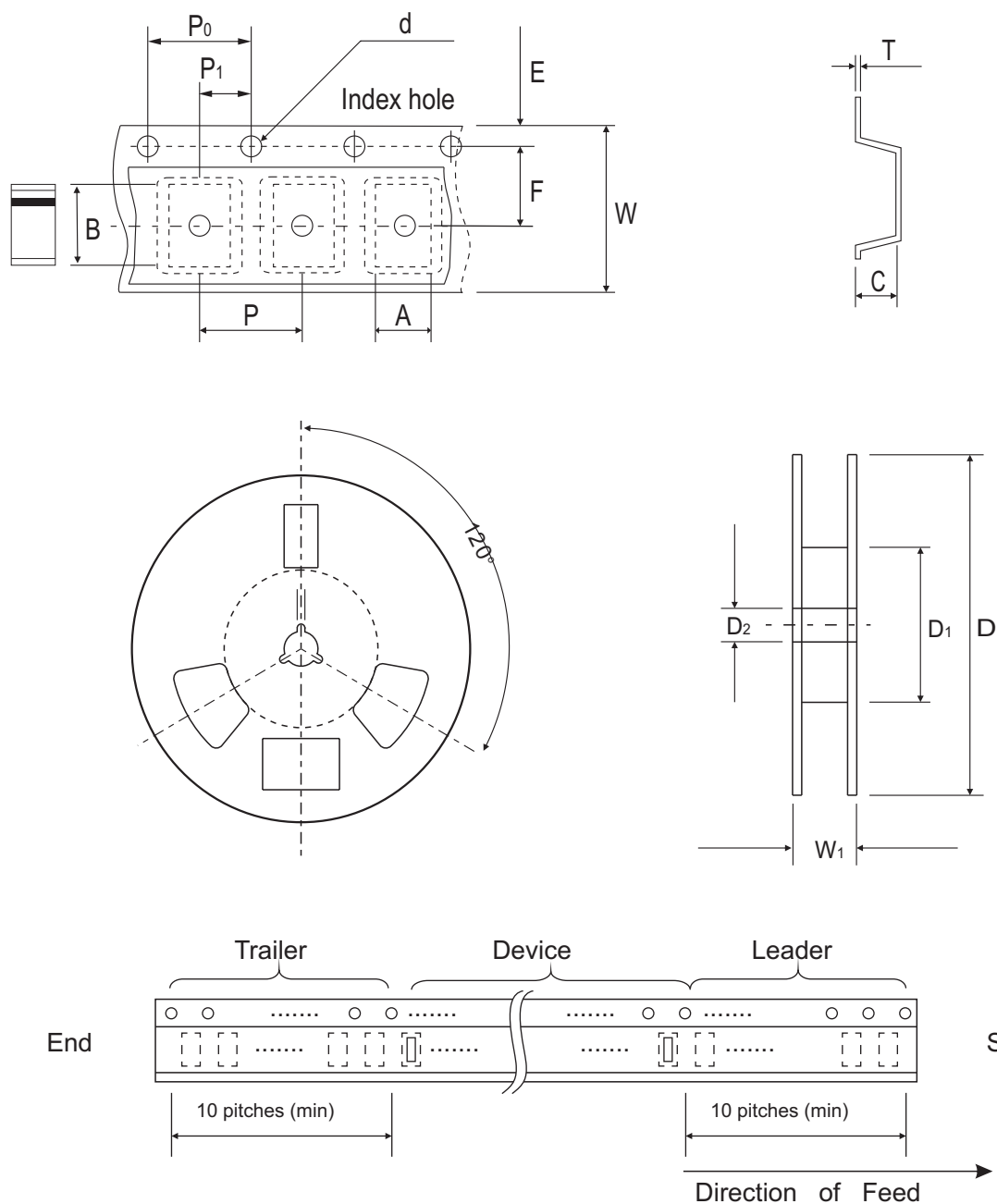


Fig.5 - Typical Junction Capacitance



Reel Taping Specification



SOD-123H	SYMBOL	A	B	C	d	D	D1	D2
	(mm)	2.00 ± 0.10	3.85 ± 0.10	1.10 ± 0.10	1.50 ± 0.10	178.00 ± 2.00	62.00 (min)	13.00 ± 0.50
	(inch)	0.079 ± 0.004	0.152 ± 0.004	0.043 ± 0.004	0.059 ± 0.004	7.007 ± 0.079	2.441 (min)	0.512 ± 0.020

SOD-123H	SYMBOL	E	F	P	P0	P1	T	W	W1
	(mm)	1.75 ± 0.10	3.50 ± 0.10	4.00 ± 0.10	4.00 ± 0.10	2.00 ± 0.10	0.23 ± 0.10	8.00 ± 0.30	11.40 ± 1.00
	(inch)	0.069 ± 0.004	0.138 ± 0.004	0.157 ± 0.004	0.157 ± 0.004	0.079 ± 0.004	0.009 ± 0.04	0.315 ± 0.012	0.449 ± 0.039

Pinning information

Pin	Simplified outline	Symbol
PIN 1 Cathode PIN 2 Anode		

Marking Code

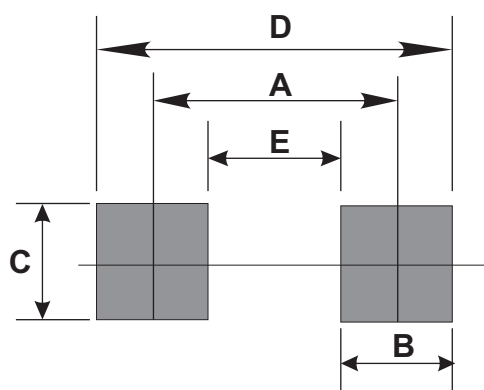
Part Number	Marking Code
CSFMT101-G	S1
CSFMT102-G	S2
CSFMT103-G	S3
CSFMT104-G	S4
CSFMT105-G	S5
CSFMT106-G	S6
CSFMT107-G	S7
CSFMT108-G	S8



xx = Product type marking code

Suggested PAD Layout

SIZE	SOD-123H	
	(mm)	(inch)
A	3.00	0.118
B	1.30	0.051
C	1.80	0.071
D	4.30	0.169
E	1.70	0.067



Standard Packaging

Case Type	REEL PACK	
	REEL (pcs)	Reel Size (inch)
SOD-123H	3,000	7